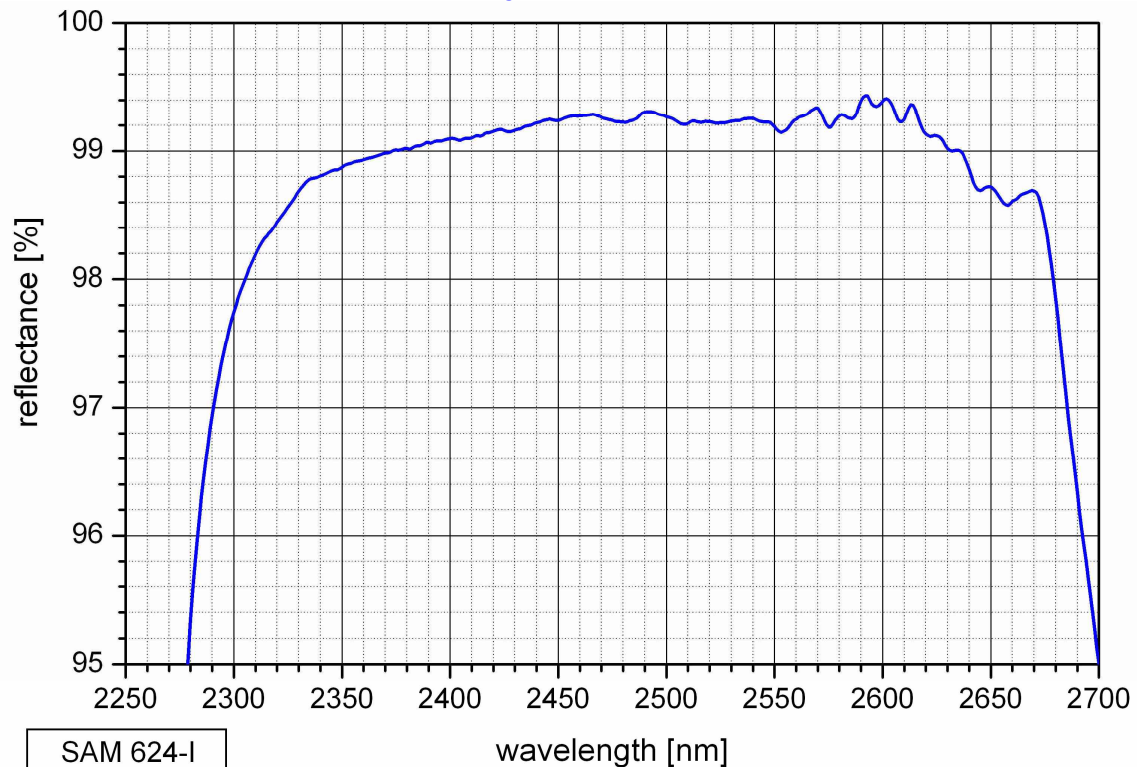


SAM™ Data Sheet SAM-2400-1-10ps-x, $\lambda = 2400 \text{ nm}$

Laser wavelength	$\lambda = 2400 \text{ nm}$
High reflection band	$\lambda = 2300 \text{ .. } 2650 \text{ nm}$
Absorbance	$A_0 = 1 \%$
Modulation depth	$\Delta R = 0.6 \%$
Non-saturable loss	$A_{ns} = 0.4 \%$
Saturation fluence	$\Phi_{sat} = 90 \mu\text{J}/\text{cm}^2$
Relaxation time constant	$\tau \sim 10 \text{ ps}$
Damage threshold	$\Phi = 1.5 \text{ mJ}/\text{cm}^2$
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	620 μm
Protection	the SAM is protected with a dielectric AR layer
Reverse design	the absorber layer is illuminated through the 620 μm thick GaAs wafer
Mounting option x denotes the type of mounting as follows:	
x = 0	unmounted
x = 12.7 g	glued on a copper heat sink with 12.7 mm diameter
x = 25.4 g	glued on a copper heat sink with 25.4 mm diameter
x = 12.7 s	soldered on a copper heat sink with 12.7 mm diameter
x = 25.4 s	soldered on a copper heat sink with 25.4 mm diameter
x = 25.0 w	soldered on a water cooled copper heat sink with 25.0 mm diameter

Low intensity spectral reflectance



SAM 624-I

wavelength [nm]

Reverse design of the SAM-2400-1-x-500fs

